

# 2SK3388

Switching Regulator and DC-DC Converter Applications  
Motor Drive Applications

- Low drain-source ON resistance:  $R_{DS(ON)} = 82 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 20 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 100 \text{ }\mu\text{A}$  ( $V_{DS} = 250 \text{ V}$ )
- Enhancement mode:  $V_{th} = 1.5 \text{ to } 3.5 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

## Absolute Maximum Ratings (Ta = 25°C)

| Characteristics                                      | Symbol         | Rating   | Unit |
|--|----------------|----------|------|
| Drain-source voltage                                 | $V_{DSS}$      | 250      | V    |
| Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ ) | $V_{DGR}$      | 250      | V    |
| Gate-source voltage                                  | $V_{GSS}$      | $\pm 20$ | V    |
| Drain current  | DC (Note 1)    | $I_D$    | 20   |
|  | Pulse (Note 1) | $I_{DP}$ | 60   |
| Drain power dissipation ( $T_c = 25^\circ\text{C}$ ) | $P_D$          | 125      | W    |
| Single pulse avalanche energy (Note 2)               | $E_{AS}$       | 487      | mJ   |
| Avalanche current                                    | $I_{AR}$       | 20       | A    |
| Repetitive avalanche energy (Note 3)                 | $E_{AR}$       | 12.5     | mJ   |
| Channel temperature                                  | $T_{ch}$       | 150      | °C   |
| Storage temperature range                            | $T_{stg}$      | -55~150  | °C   |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## Thermal Characteristics

| Characteristics                     | Symbol         | Max  | Unit |
|-------------------------------------|----------------|------|------|
| Thermal resistance, channel to case | $R_{th(ch-c)}$ | 1.00 | °C/W |

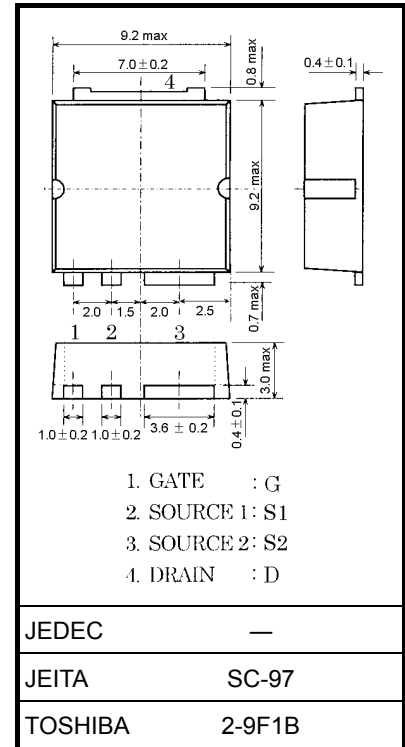
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 50 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 2.06 \text{ mH}$ ,  $I_{AR} = 20 \text{ A}$ ,  $R_G = 25 \text{ }\Omega$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.

Unit: mm

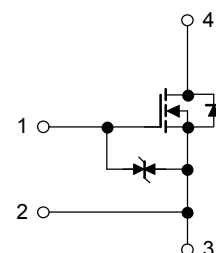


Weight: 0.74 g (typ.)

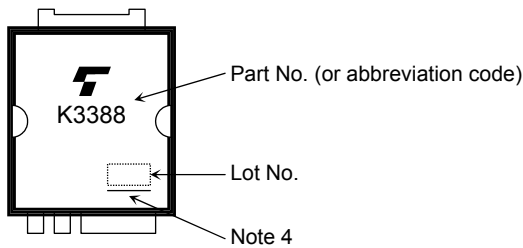
## Circuit Configuration

Notice:

Please use the S1 pin for gate input signal return. Make sure that the main current flows into the S2 pin.



## Marking



Note 4: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

## Electrical Characteristics (Note 5) (Ta = 25°C)

| Characteristics                                 |               | Symbol        | Test Condition   | Min | Typ. | Max      | Unit             |
|---|---------------|---------------|--|-----|------|----------|------------------|
| Gate leakage current                            |               | $I_{GSS}$     | $V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$                        | —   | —    | $\pm 10$ | $\mu\text{A}$    |
| Drain cut-off current                           |               | $I_{DSS}$     | $V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$                           | —   | —    | 100      | $\mu\text{A}$    |
| Drain-source breakdown voltage                  |               | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$                              | 250 | —    | —        | V                |
| Gate threshold voltage                          |               | $V_{th}$      | $V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$                              | 1.5 | —    | 3.5      | V                |
| Drain-source ON resistance                      |               | $R_{DS(ON)}$  | $V_{GS} = 10\text{ V}, I_D = 10\text{ A}$                              | —   | 82   | 105      | $\text{m}\Omega$ |
| Forward transfer admittance                     |               | $ Y_{fs} $    | $V_{DS} = 10\text{ V}, I_D = 10\text{ A}$                              | 10  | 20   | —        | S                |
| Input capacitance                               |               | $C_{iss}$     | $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$          | —   | 4000 | —        | pF               |
| Reverse transfer capacitance                    |               | $C_{rss}$     |  | —   | 300  | —        |                  |
| Output capacitance                              |               | $C_{oss}$     |  | —   | 1000 | —        |                  |
| Switching time                                  | Rise time     | $t_r$         |  | —   | 7    | —        | ns               |
|   | Turn-on time  | $t_{on}$      |  | —   | 20   | —        |                  |
|   | Fall time     | $t_f$         |  | —   | 25   | —        |                  |
|   | Turn-off time | $t_{off}$     |  | —   | 145  | —        |                  |
| Total gate charge (gate-source plus gate-drain) |               | $Q_g$         | $V_{DD} \approx 200\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$ | —   | 100  | —        | nC               |
| Gate-source charge                              |               | $Q_{gs}$      |  | —   | 70   | —        |                  |
| Gate-drain ("miller") charge                    |               | $Q_{gd}$      |  | —   | 30   | —        |                  |

Note 5: Connect the S1 and S2 pins together, and ground them except during switching time measurement.

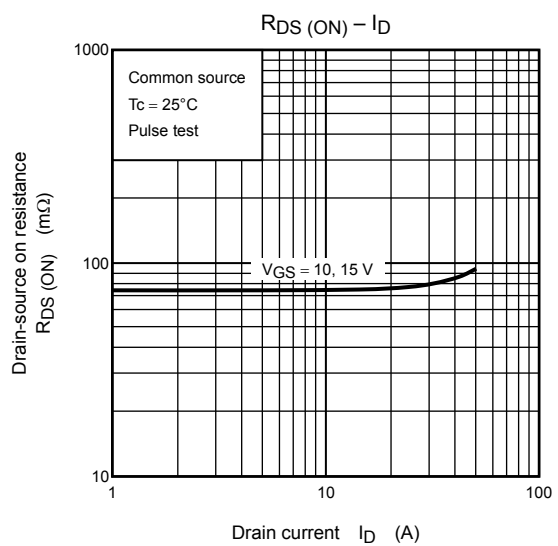
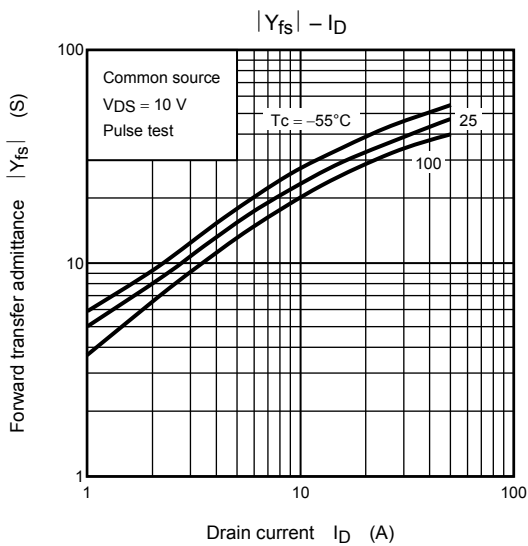
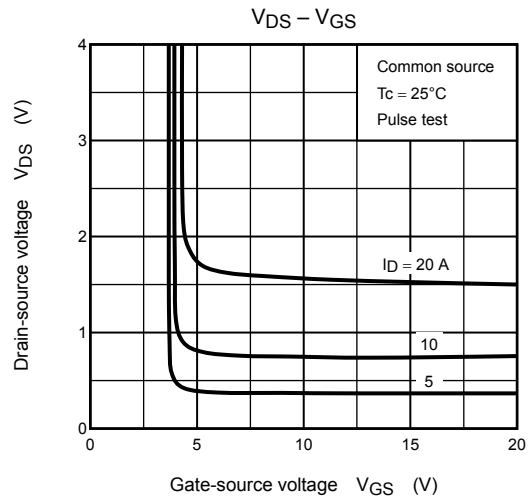
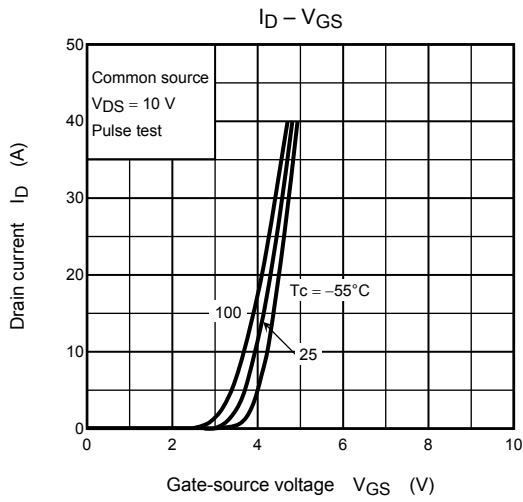
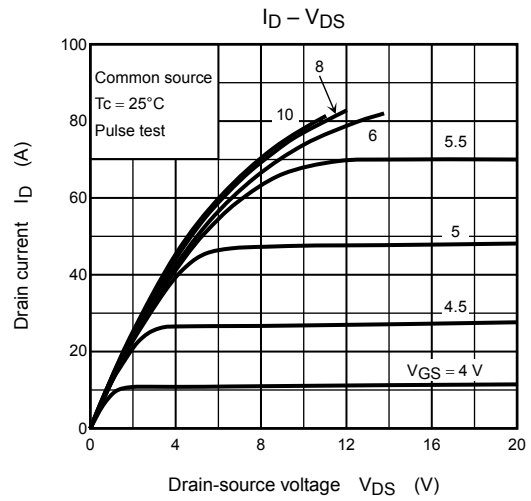
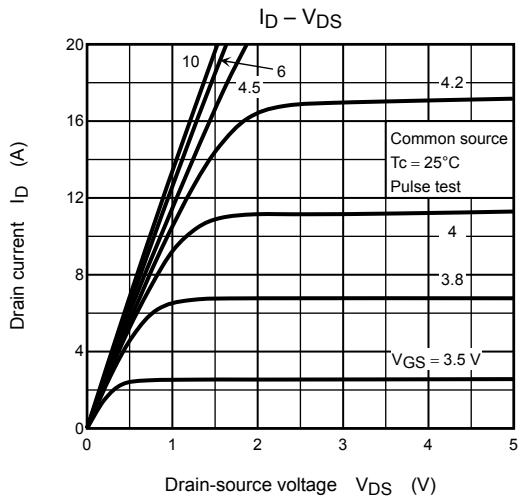
## Source-Drain Ratings and Characteristics (Note 6) (Ta = 25°C)

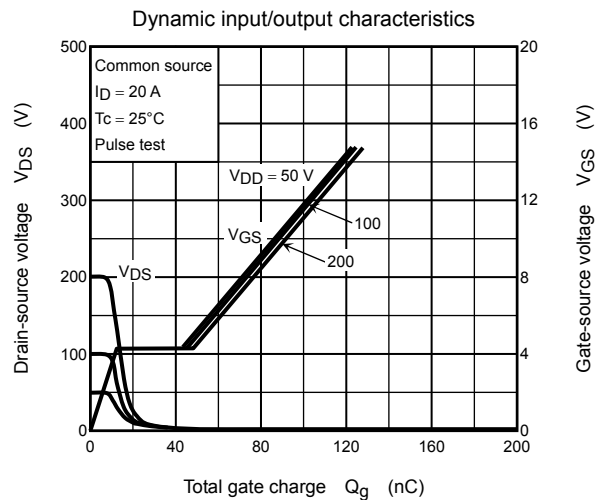
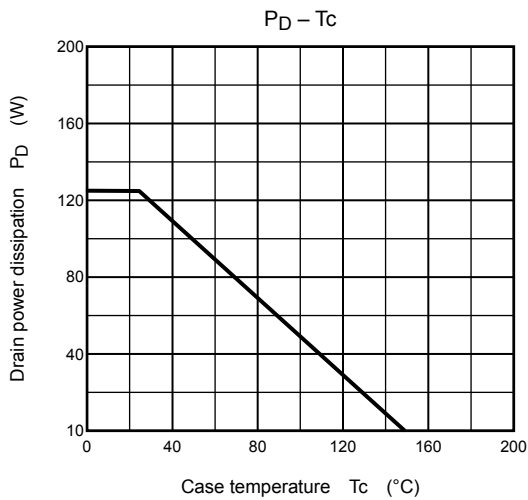
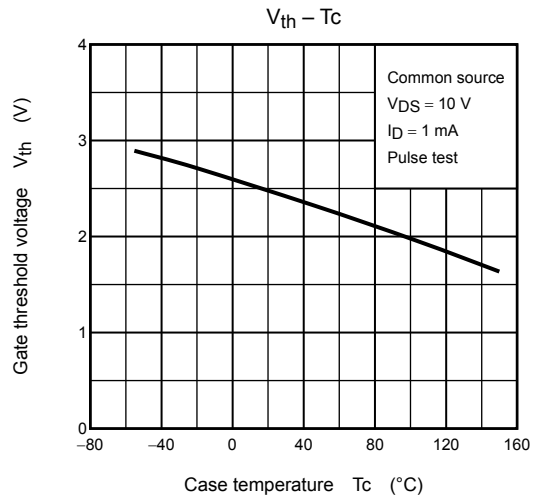
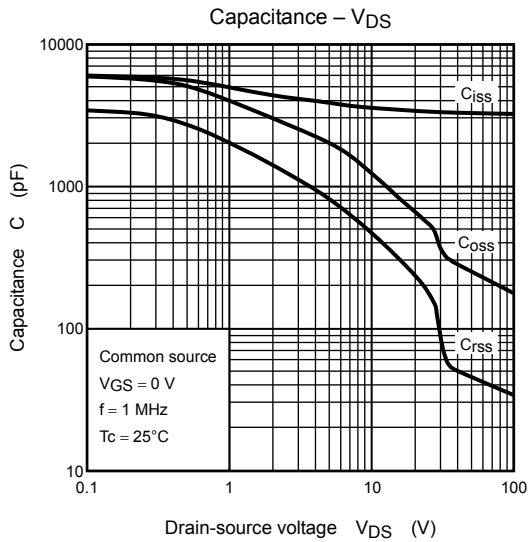
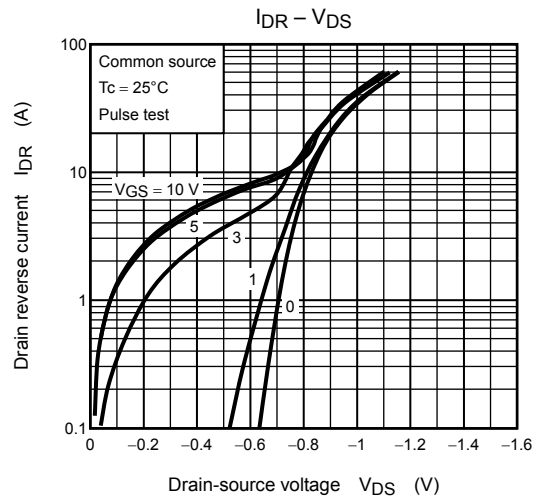
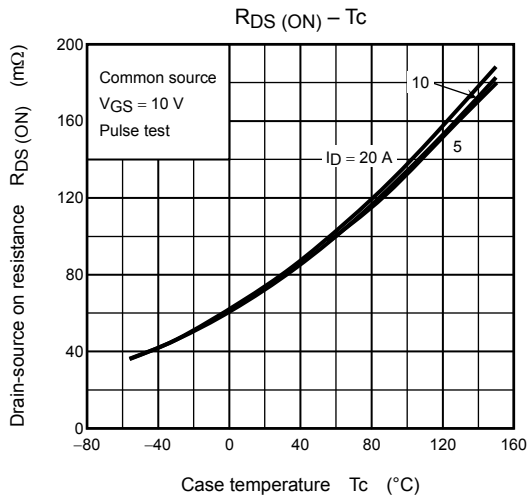
| Characteristics                                   | Symbol     | Test Condition   | Min | Typ. | Max  | Unit          |
|---|------------|--|-----|------|------|---------------|
| Continuous drain reverse current (Note 1, Note 6) | $I_{DR1}$  | —  | —   | —    | 20   | A             |
| Pulse drain reverse current (Note 1, Note 6)      | $I_{DRP1}$ | —  | —   | —    | 60   | A             |
| Continuous drain reverse current (Note 1, Note 6) | $I_{DR2}$  | —  | —   | —    | 1    | A             |
| Pulse drain reverse current (Note 1, Note 6)      | $I_{DRP2}$ | —  | —   | —    | 4    | A             |
| Forward voltage (diode)                           | $V_{DS2F}$ | $I_{DR1} = 20\text{ A}, V_{GS} = 0\text{ V}$                                       | —   | —    | -2.0 | V             |
| Reverse recovery time                             | $t_{rr}$   | $I_{DR} = 20\text{ A}, V_{GS} = 0\text{ V}, dI_{DR}/dt = 100\text{ A}/\mu\text{s}$ | —   | 300  | —    | ns            |
| Reverse recovery charge                           | $Q_{rr}$   |  | —   | 3.3  | —    | $\mu\text{C}$ |

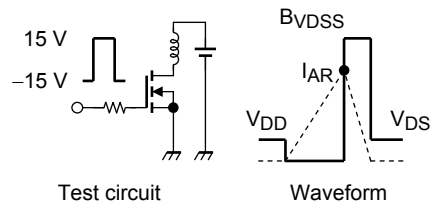
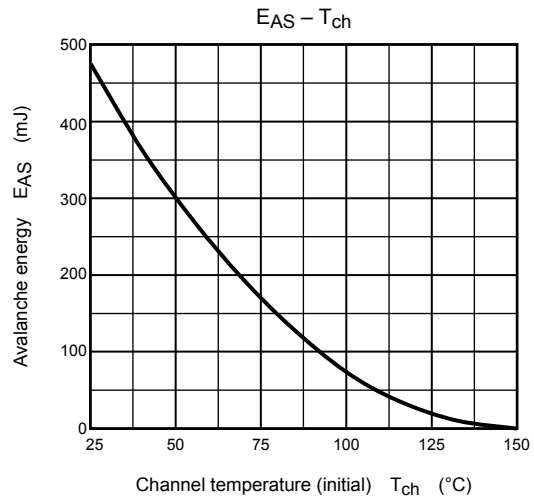
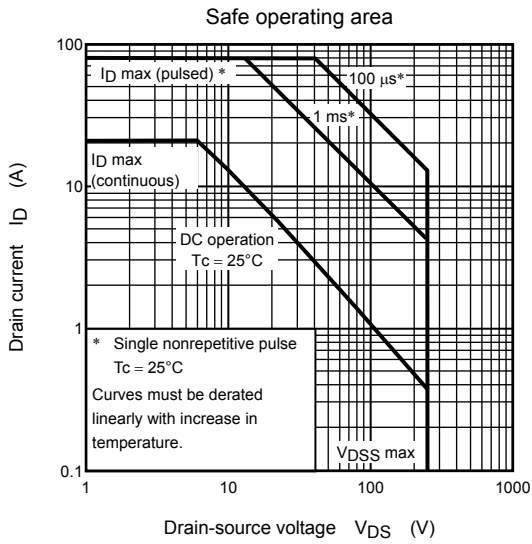
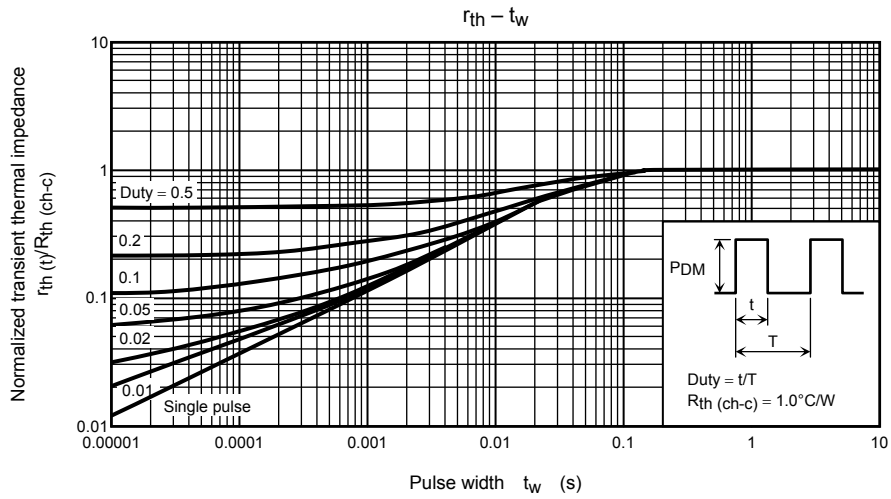
Note 6:  $I_{DR1}, I_{DRP1}$ : Current flowing between the drain and the S2 pin. Ensure that the S1 pin is left open.

$I_{DR2}, I_{DRP2}$ : Current flowing between the drain and the S1 pin. Ensure that the S2 pin is left open.

Unless otherwise specified, connect the S1 and S2 pins together, and ground them.







$R_G = 25 \Omega$   
 $V_{DD} = 50 \text{ V}, L = 2.06 \text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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